

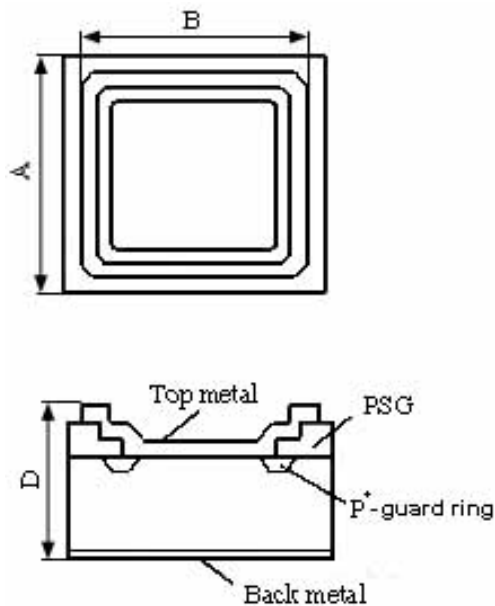
# SCHOTTKY DIODE KDN-30040A.

PRELIMINARY



Rev.1. Feb. 2010

	<b>30A/40V. Die Size-130mil.</b>			
<b>Electrical Characteristics</b>	<b>Symbol</b>	<b>Unit</b>	<b>Spec. Limit</b>	<b>Die Sort</b>
Breakdown Voltage @ $I_R=10mA$	$V_{BR}$	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	30,0	-
DC Forward Voltage @ 25°C, $I_F=30,0A$ @ 25°C, $I_F=25,0A$	$V_F$	V	0,57 0,54	0,55 0,52
Maximum Reverse Current @ 25°C, $V_R=45V$ 25°C, $V_R=40V$ 125°C, $V_R=40V$	$I_R$	mA	- 0,50 350	0,80 0,40 300,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	300	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<150°C$ .	$I_{RRM}$	A	5,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	$T_J$	°C	150	



DIM	ITEM	µm
$A_x$ $A_y$	Wafer Form Die Size	3300 3300
$B_x$ $B_y$	Top Metal Size	3160 3160
D	Thickness	350max.
Scribe line Width		80

Top metal: a) Ti-Ni-Ag – for Soldering;  
b) Al.- for Wire Bonding.  
Back metal: Ti-Ni-Ag.